Ordering number: EN 3794

SANYO No.3794

2SC4441

NPN Triple Diffused Planar Silicon Transistor

Very High-Definition Monocuro Display Horizontal Deflection Output Applications

Features

- High reliability(Adoption of HVP process).
- High fast.
- High breakdown voltage.
- Wide ASO.
- Adoption of MBIT process.
- Micaless package facilitating mounting.

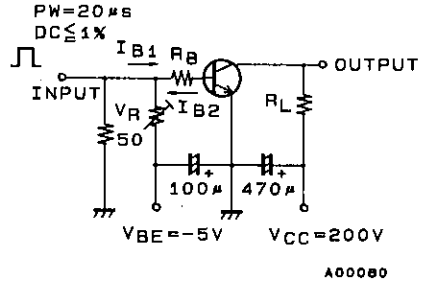
Absolute Maximum Ratings at Ta = 25°C

				unit
Collector-to-Base Voltage	V_{CBO}		600	V
Collector-to-Emitter Voltage	V_{CEO}		400	V
Emitter-to-Base Voltage	V_{EBO}		7	V
Collector Current	I_C		10	A
Peak Collector Current	i_{cp}	PW≦300μs, Duty Cycle≦10%	20	A
Collector Dissipation	P_C		2.0	W
		Tc = 25°C	35	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		−55 to +150	°C

Electrical Characteristics at Ta = 25°C

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	V_{CB} = 400V, I_E = 0			10	μA
	I_{CES}	V_{CE} = 600V			0.5	mA
Collector Sustain Voltage	$V_{CEO(sus)}$	I_C = 100mA, I_B = 0	400			V
Emitter Cutoff Current	I_{EBO}	V_{EB} = 5V, I_C = 0			1	mA
C-E Saturation Voltage	$V_{CE(sat)}$	I_C = 6A, I_B = 1.2A			0.8	V
B-E Saturation Voltage	$V_{BE(sat)}$	I_C = 6A, I_B = 1.2A			1.5	V
DC Current Gain	$h_{FE(1)}$	V_{CE} = 5V, I_C = 1.2A	15			
	$h_{FE(2)}$	V_{CE} = 5V, I_C = 6A	10		20	
Gain-Bandwidth Product	f_T	V_{CE} = 10V, I_C = 1.2A		20		MHz
Storage Time	t_{stg}	I_C = 7A, I_{B1} = 1.4A			3.0	μs
Fall Time	t_f	I_{B2} = −2.8A, R_L = 28.6Ω			0.2	μs
		V_{CC} = 200V				

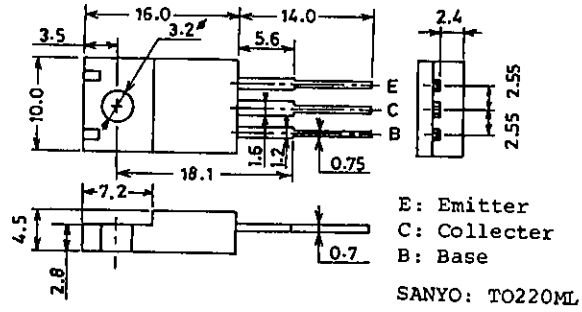
Switching Time Test Circuits



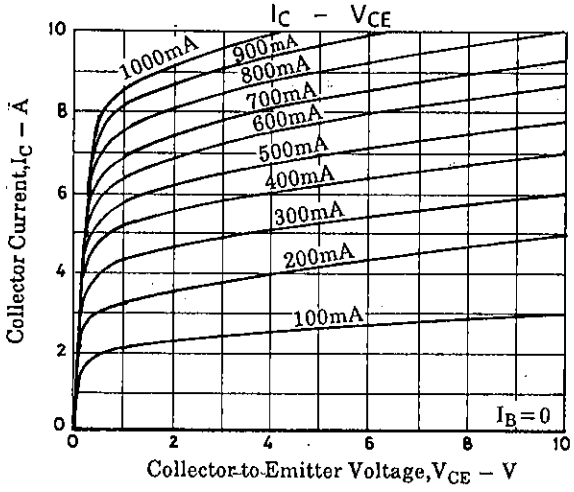
Unit (resistance:Ω, capacitance:F)

Package Dimensions

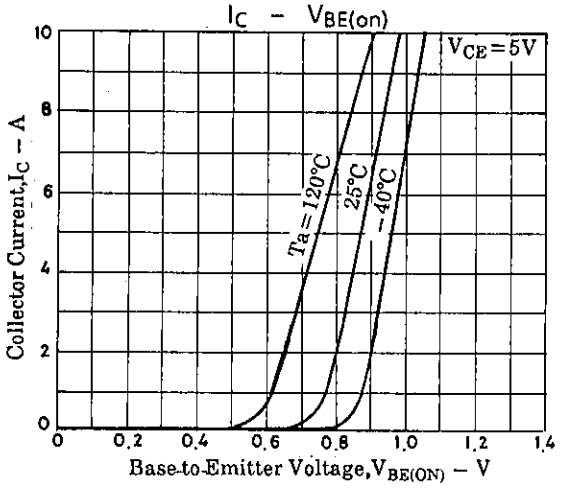
(unit: mm) 2041



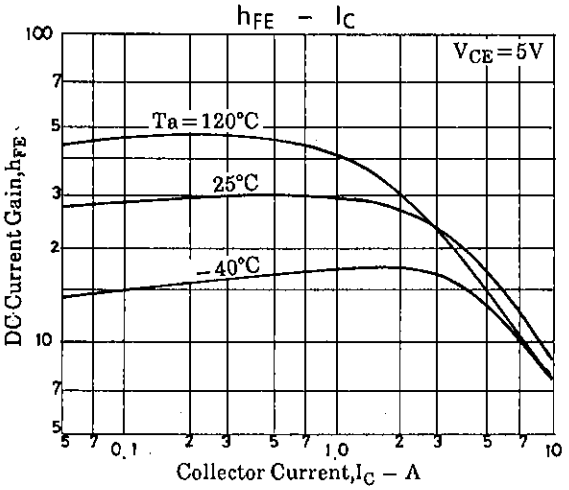
I_C – V_{CE}



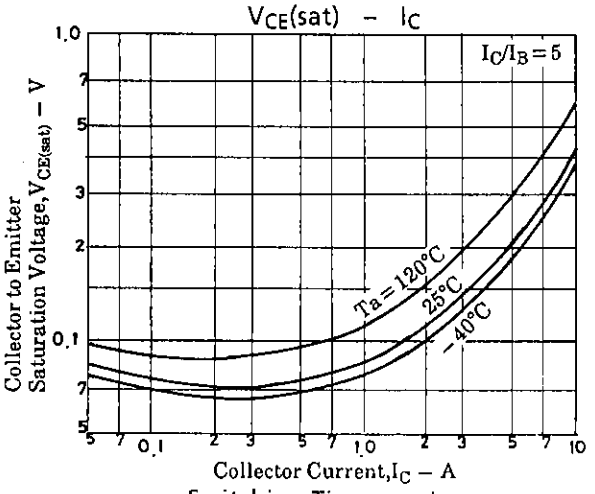
I_C – $V_{BE(on)}$



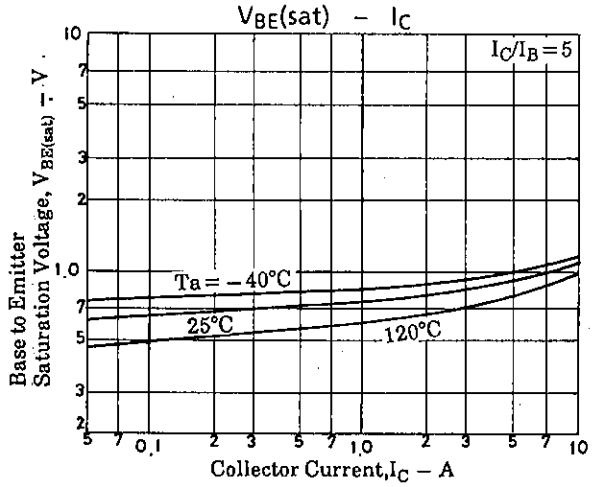
h_{FE} – I_C



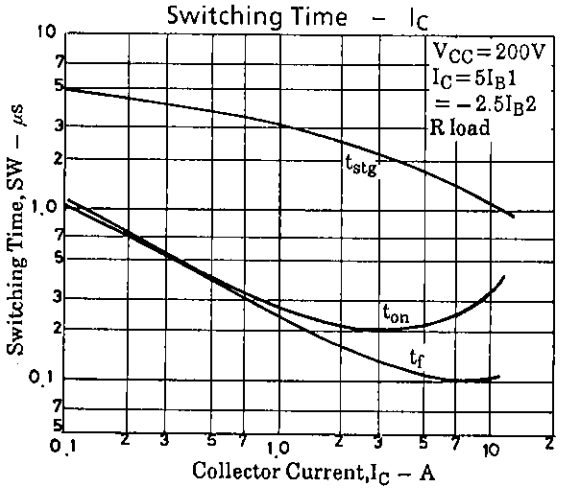
$V_{CE(sat)}$ – I_C



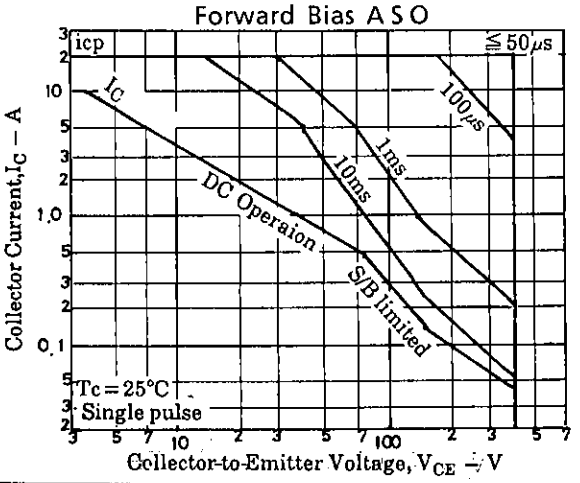
$V_{BE(sat)}$ – I_C



Switching Time – I_C



Forward Bias A S O



Reverse Bias A S O